

IHM-B module with Trench/Fieldstop IGBT3 and emitter controlled 3 diode

Features

- Electrical features
 - $V_{CES} = 3300\text{ V}$
 - $I_{C\text{nom}} = 1000\text{ A} / I_{CRM} = 2000\text{ A}$
 - Unbeatable robustness
 - High DC stability
 - High short-circuit capability
 - Low $V_{CE,sat}$
 - $T_{vj,op} = 150^{\circ}\text{C}$
 - $V_{CE,sat}$ with positive temperature coefficient
- Mechanical features
 - ALSiC base plate for increased thermal cycling capability
 - Package with CTI > 600
 - IHM B housing
 - Isolated base plate



Potential applications

- Chopper applications
- Medium-voltage converters
- Motor drives
- Traction drives
- UPS systems
- Wind turbines

Product validation

- Qualified for industrial applications according to the relevant tests of IEC 60747, 60749 and 60068

Description

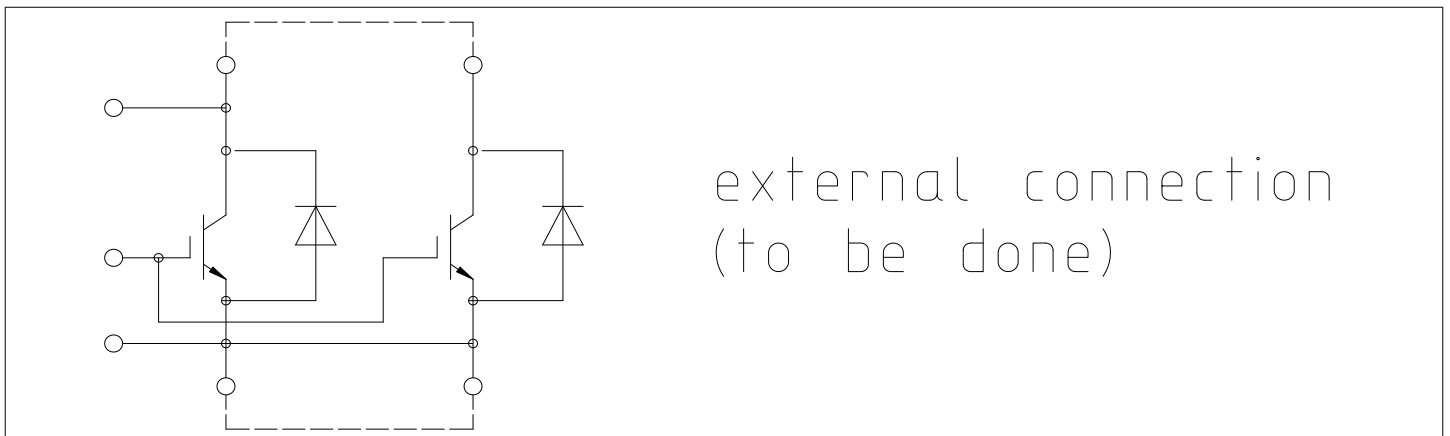


Table of contents

	Description	1
	Features	1
	Potential applications	1
	Product validation	1
	Table of contents	2
1	Package	3
2	IGBT, Inverter	3
3	Diode, Inverter	5
4	Characteristics diagrams	7
5	Circuit diagram	10
6	Package outlines	11
7	Module label code	12
	Revision history	13
	Disclaimer	14

1 Package

Table 1 Insulation coordination

Parameter	Symbol	Note or test condition	Values	Unit
Isolation test voltage	V_{ISOL}	RMS, $f = 50$ Hz, $t = 1$ min	6.0	kV
Partial discharge extinction voltage	V_{isol}	RMS, $f = 50$ Hz, $Q_{PD} \leq 10$ pC	2.6	kV
DC stability	$V_{CE(D)}$	$T_{vj}=25^{\circ}\text{C}$, 100 Fit	2100	V
Material of module baseplate			AlSiC	
Creepage distance	d_{Creep}	terminal to heatsink	32.2	mm
Clearance	d_{Clear}	terminal to heatsink	19.1	mm
Comparative tracking index	CTI		>600	

Table 2 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Stray inductance module	L_{SCE}			9		nH
Module lead resistance, terminals - chip	$R_{CC'+EE'}$	$T_C=25^{\circ}\text{C}$, per switch		0.19		m Ω
Storage temperature	T_{stg}		-40		150	$^{\circ}\text{C}$
Mounting torque for module mounting	M	- Mounting according to valid application note	M6, Screw	4.25	5.75	Nm
Terminal connection torque	M	- Mounting according to valid application note	M4, Screw	1.8	2.1	Nm
			M8, Screw	8	10	
Weight	G			800		g

2 IGBT, Inverter

Table 3 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Collector-emitter voltage	V_{CES}		$T_{vj} = -40^{\circ}\text{C}$	3300	V
			$T_{vj} = 150^{\circ}\text{C}$	3300	
Continuous DC collector current	I_{CDC}	$T_{vj\ max} = 150^{\circ}\text{C}$	$T_C = 95^{\circ}\text{C}$	1000	A
Repetitive peak collector current	I_{CRM}	$t_p = 1$ ms		2000	A
Gate-emitter peak voltage	V_{GES}			± 20	V

Table 4 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Collector-emitter saturation voltage	$V_{CE\ sat}$	$I_C = 1000\ A, V_{GE} = 15\ V$	$T_{vj} = 25\ ^\circ C$		2.40	2.85	V
			$T_{vj} = 125\ ^\circ C$		2.95	3.50	
			$T_{vj} = 150\ ^\circ C$		3.10		
Gate threshold voltage	V_{GEth}	$I_C = 48\ mA, V_{CE} = V_{GE}, T_{vj} = 25\ ^\circ C$	5.20	5.80	6.40	V	
Gate charge	Q_G	$V_{GE} = \pm 15\ V, V_{CE} = 1800\ V$		28		μC	
Internal gate resistor	R_{Gint}	$T_{vj} = 25\ ^\circ C$		0.63		Ω	
Input capacitance	C_{ies}	$f = 1000\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$		190		nF	
Reverse transfer capacitance	C_{res}	$f = 1000\ kHz, T_{vj} = 25\ ^\circ C, V_{CE} = 25\ V, V_{GE} = 0\ V$		4		nF	
Collector-emitter cut-off current	I_{CES}	$V_{CE} = 3300\ V, V_{GE} = 0\ V$	$T_{vj} = 25\ ^\circ C$			5	mA
Gate-emitter leakage current	I_{GES}	$V_{CE} = 0\ V, V_{GE} = 20\ V, T_{vj} = 25\ ^\circ C$				400	nA
Turn-on delay time (inductive load)	t_{don}	$I_C = 1000\ A, V_{CE} = 1800\ V, V_{GE} = \pm 15\ V, R_{Gon} = 0.75\ \Omega, C_{GE} = 220\ nF$	$T_{vj} = 25\ ^\circ C$	0.360		μs	
			$T_{vj} = 125\ ^\circ C$	0.400			
			$T_{vj} = 150\ ^\circ C$	0.400			
Rise time (inductive load)	t_r	$I_C = 1000\ A, V_{CE} = 1800\ V, V_{GE} = \pm 15\ V, R_{Gon} = 0.75\ \Omega, C_{GE} = 220\ nF$	$T_{vj} = 25\ ^\circ C$	0.370		μs	
			$T_{vj} = 125\ ^\circ C$	0.400			
			$T_{vj} = 150\ ^\circ C$	0.400			
Turn-off delay time (inductive load)	t_{doff}	$I_C = 1000\ A, V_{CE} = 1800\ V, V_{GE} = \pm 15\ V, R_{Goff} = 4.1\ \Omega, C_{GE} = 220\ nF$	$T_{vj} = 25\ ^\circ C$	4.100		μs	
			$T_{vj} = 125\ ^\circ C$	4.300			
			$T_{vj} = 150\ ^\circ C$	4.300			
Fall time (inductive load)	t_f	$I_C = 1000\ A, V_{CE} = 1800\ V, V_{GE} = \pm 15\ V, R_{Goff} = 4.1\ \Omega, C_{GE} = 220\ nF$	$T_{vj} = 25\ ^\circ C$	0.400		μs	
			$T_{vj} = 125\ ^\circ C$	0.400			
			$T_{vj} = 150\ ^\circ C$	0.400			
Turn-on time (resistive load)	t_{on_R}	$I_C = 500\ A, V_{CE} = 2000\ V, V_{GE} = \pm 15\ V, R_{Gon} = 0.75\ \Omega, C_{GE} = 220\ nF$	$T_{vj} = 25\ ^\circ C$	1.32		μs	
Turn-on energy loss per pulse	E_{on}	$I_C = 1000\ A, V_{CE} = 1800\ V, L_\sigma = 85\ nH, V_{GE} = \pm 15\ V, R_{Gon} = 0.75\ \Omega, C_{GE} = 220\ nF, di/dt = 3000\ A/\mu s (T_{vj} = 150\ ^\circ C)$	$T_{vj} = 25\ ^\circ C$	1550		mJ	
			$T_{vj} = 125\ ^\circ C$	2150			
			$T_{vj} = 150\ ^\circ C$	2400			

(table continues...)

Table 4 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Turn-off energy loss per pulse	E_{off}	$I_C = 1000\text{ A}$, $V_{CE} = 1800\text{ V}$, $L_\sigma = 85\text{ nH}$, $V_{GE} = \pm 15\text{ V}$, $R_{Goff} = 4.1\ \Omega$, $C_{GE} = 220\text{ nF}$, $dv/dt = 1550\text{ V}/\mu\text{s}$ ($T_{vj} = 150\text{ }^\circ\text{C}$)	$T_{vj} = 25\text{ }^\circ\text{C}$	1600		mJ
			$T_{vj} = 125\text{ }^\circ\text{C}$	1950		
			$T_{vj} = 150\text{ }^\circ\text{C}$	2050		
SC data	I_{SC}	$V_{GE} \leq 15\text{ V}$, $V_{CC} = 2500\text{ V}$, $V_{CEmax} = V_{CES} - L_{sCE} * di/dt$	$t_p \leq 10\ \mu\text{s}$, $T_{vj} = 150\text{ }^\circ\text{C}$	4300		A
Thermal resistance, junction to case	R_{thJC}	per IGBT			11.1	K/kW
Thermal resistance, case to heat sink	R_{thCH}	per IGBT, $\lambda_{grease} = 1\text{ W}/(\text{m}^2\text{K})$		14.5		K/kW
Temperature under switching conditions	$T_{vj\text{ op}}$		-40		150	$^\circ\text{C}$

3 Diode, Inverter

Table 5 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit	
Repetitive peak reverse voltage	V_{RRM}		$T_{vj} = -40\text{ }^\circ\text{C}$	3300	V
			$T_{vj} = 150\text{ }^\circ\text{C}$	3300	
Continuous DC forward current	I_F		1000	A	
Repetitive peak forward current	I_{FRM}	$t_p = 1\text{ ms}$	2000	A	
I^2t - value	I^2t	$t_p = 10\text{ ms}$, $V_R = 0\text{ V}$	$T_{vj} = 125\text{ }^\circ\text{C}$	375	kA ² s
			$T_{vj} = 150\text{ }^\circ\text{C}$	325	
Maximum power dissipation	P_{RQM}	$T_{vj} = 150\text{ }^\circ\text{C}$	1600	kW	
Minimum turn-on time	t_{onmin}		10	μs	

Table 6 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit	
			Min.	Typ.	Max.		
Forward voltage	V_F	$I_F = 1000\text{ A}$, $V_{GE} = 0\text{ V}$	$T_{vj} = 25\text{ }^\circ\text{C}$		2.25	2.85	V
			$T_{vj} = 125\text{ }^\circ\text{C}$		2.20	2.75	
			$T_{vj} = 150\text{ }^\circ\text{C}$		2.20		

(table continues...)

Table 6 (continued) Characteristic values

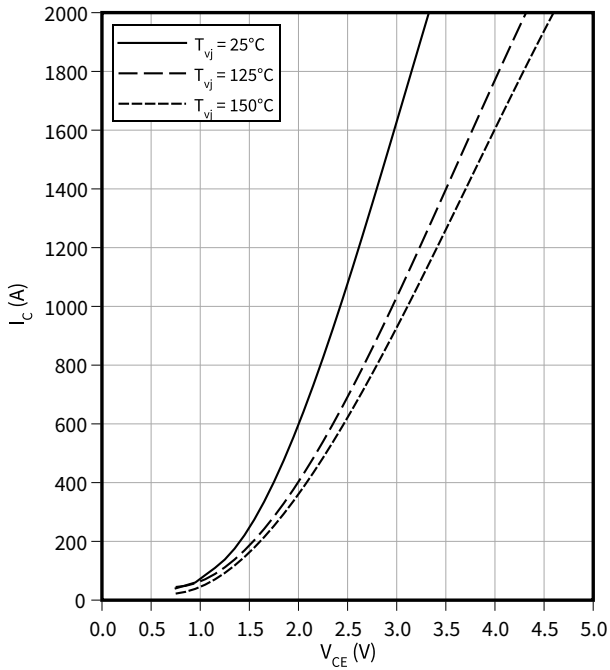
Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Peak reverse recovery current	I_{RM}	$V_R = 1800\text{ V}$, $I_F = 1000\text{ A}$, $V_{GE} = -15\text{ V}$, $-di_F/dt = 3000\text{ A}/\mu\text{s}$ ($T_{vj} = 150\text{ }^\circ\text{C}$)	$T_{vj} = 25\text{ }^\circ\text{C}$	1100		A
			$T_{vj} = 125\text{ }^\circ\text{C}$	1200		
			$T_{vj} = 150\text{ }^\circ\text{C}$	1250		
Recovered charge	Q_r	$V_R = 1800\text{ V}$, $I_F = 1000\text{ A}$, $V_{GE} = -15\text{ V}$, $-di_F/dt = 3000\text{ A}/\mu\text{s}$ ($T_{vj} = 150\text{ }^\circ\text{C}$)	$T_{vj} = 25\text{ }^\circ\text{C}$	1000		μC
			$T_{vj} = 125\text{ }^\circ\text{C}$	1750		
			$T_{vj} = 150\text{ }^\circ\text{C}$	1950		
Reverse recovery energy	E_{rec}	$V_R = 1800\text{ V}$, $I_F = 1000\text{ A}$, $V_{GE} = -15\text{ V}$, $-di_F/dt = 3000\text{ A}/\mu\text{s}$ ($T_{vj} = 150\text{ }^\circ\text{C}$)	$T_{vj} = 25\text{ }^\circ\text{C}$	1100		mJ
			$T_{vj} = 125\text{ }^\circ\text{C}$	2100		
			$T_{vj} = 150\text{ }^\circ\text{C}$	2500		
Thermal resistance, junction to case	R_{thJC}	per diode			19.8	K/kW
Thermal resistance, case to heat sink	R_{thCH}	per diode, $\lambda_{grease} = 1\text{ W}/(\text{m}^*\text{K})$		16.5		K/kW
Temperature under switching conditions	$T_{vj\text{ op}}$		-40		150	$^\circ\text{C}$

4 Characteristics diagrams

output characteristic (typical), IGBT, Inverter

$$I_C = f(V_{CE})$$

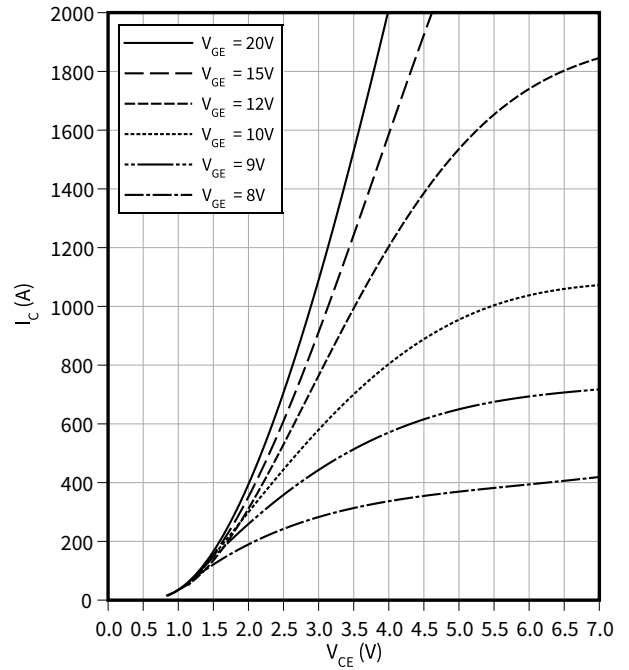
$$V_{GE} = 15 \text{ V}$$



output characteristic (typical), IGBT, Inverter

$$I_C = f(V_{CE})$$

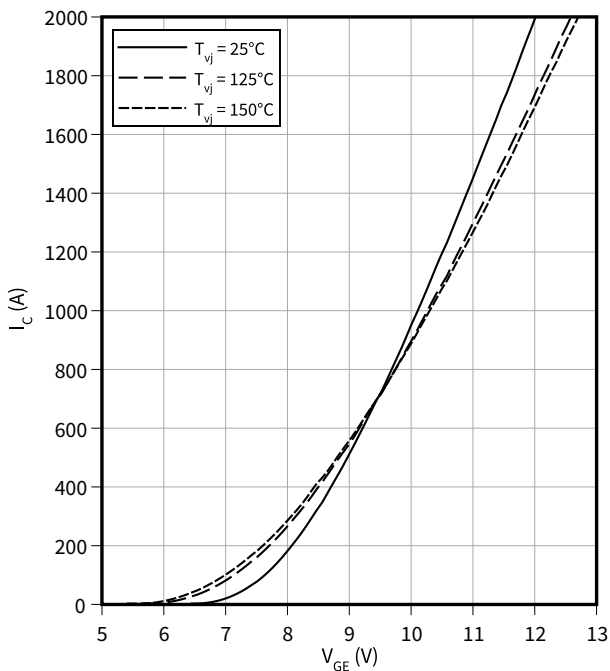
$$T_{vj} = 150 \text{ °C}$$



transfer characteristic (typical), IGBT, Inverter

$$I_C = f(V_{GE})$$

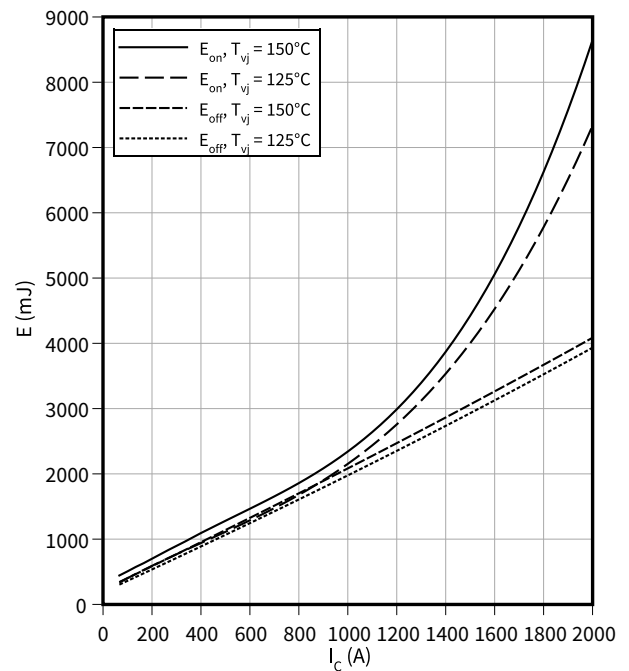
$$V_{CE} = 20 \text{ V}$$



switching losses (typical), IGBT, Inverter

$$E = f(I_C)$$

$$R_{Goff} = 4.1 \text{ } \Omega, R_{Gon} = 0.75 \text{ } \Omega, V_{GE} = \pm 15 \text{ V}, C_{GE} = 220 \text{ nF}, V_{CE} = 1800 \text{ V}$$

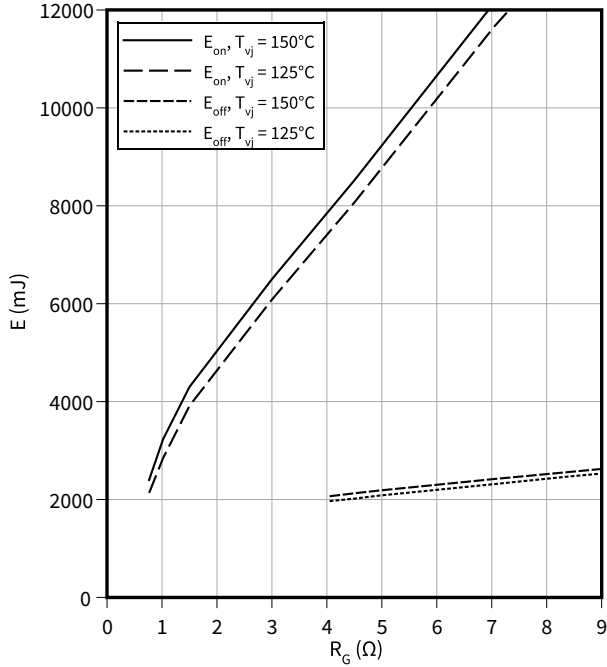


4 Characteristics diagrams

switching losses (typical), IGBT, Inverter

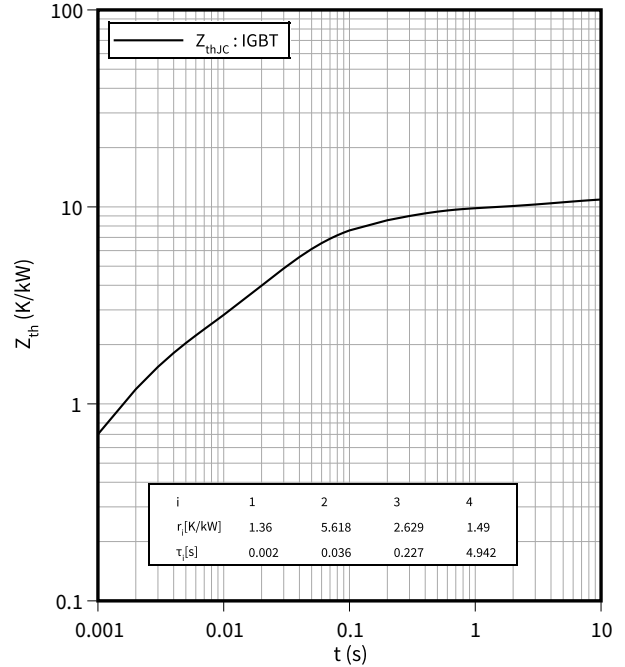
$E = f(R_G)$

$V_{GE} = \pm 15 \text{ V}$, $I_C = 1000 \text{ A}$, $C_{GE} = 220 \text{ nF}$, $V_{CE} = 1800 \text{ V}$



transient thermal impedance , IGBT, Inverter

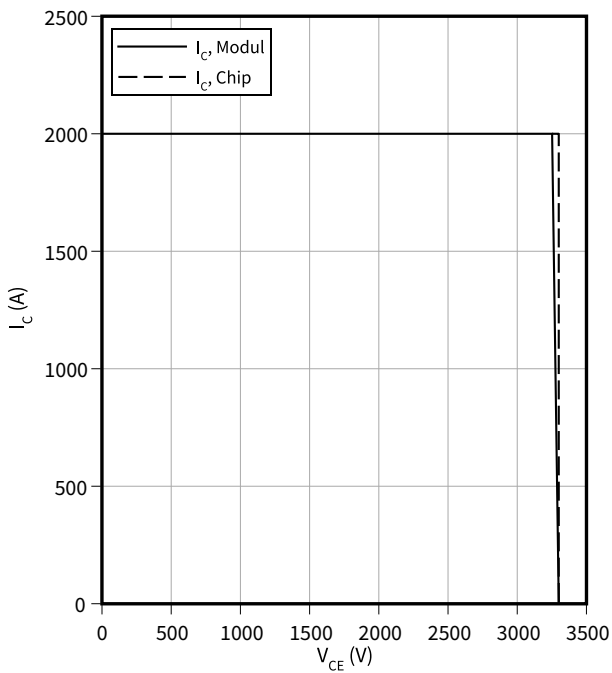
$Z_{th} = f(t)$



reverse bias safe operating area (RBSOA), IGBT, Inverter

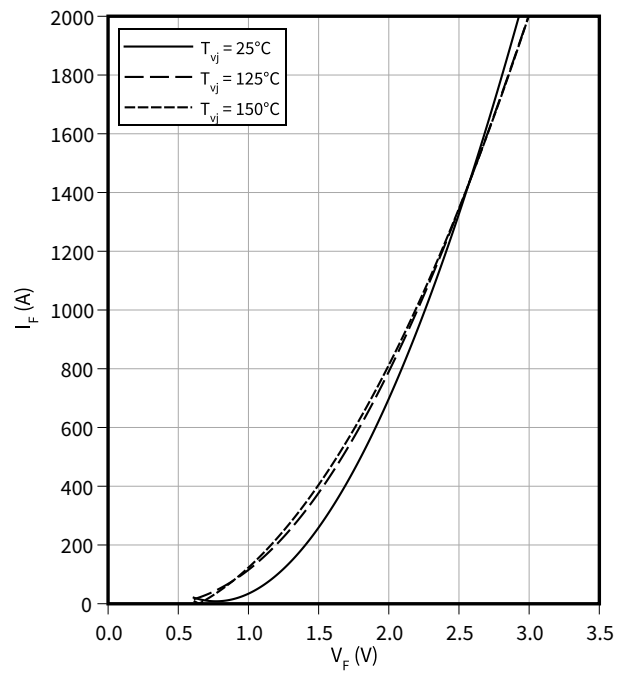
$I_C = f(V_{CE})$

$R_{Goff} = 4.1 \Omega$, $V_{GE} = \pm 15 \text{ V}$, $C_{GE} = 220 \text{ nF}$, $T_{vj} = 150 \text{ °C}$



forward characteristic (typical), Diode, Inverter

$I_F = f(V_F)$

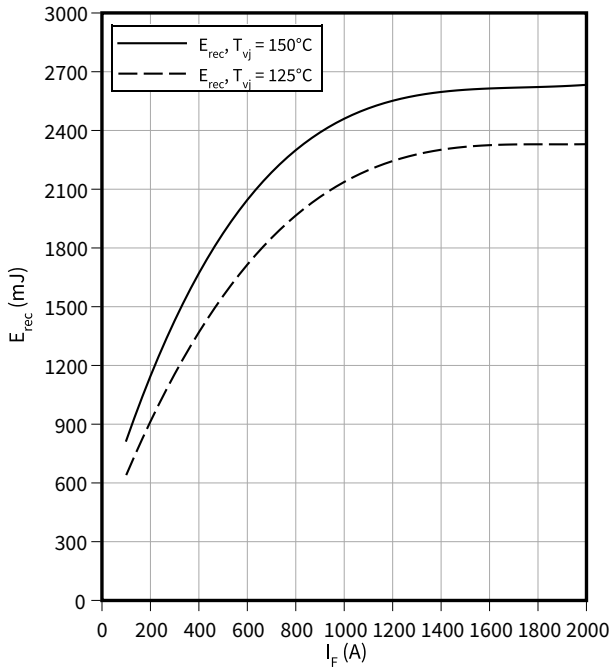


4 Characteristics diagrams

switching losses (typical), Diode, Inverter

$E_{rec} = f(I_F)$

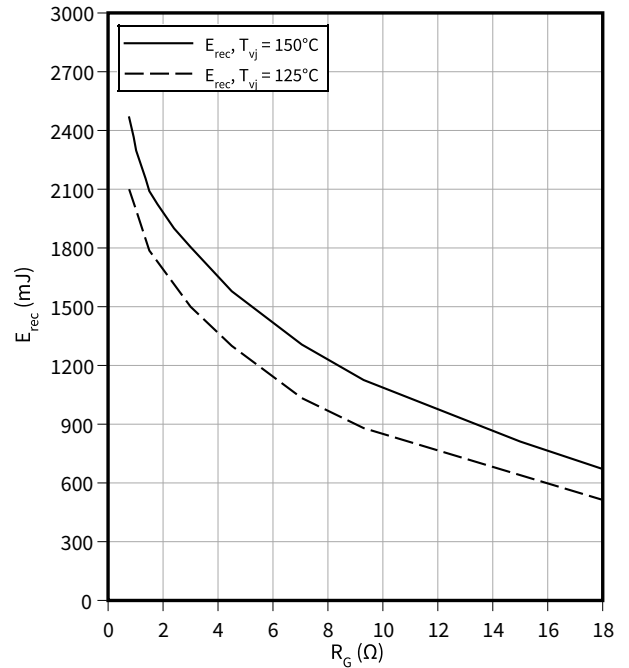
$V_{CE} = 1800\text{ V}$, $R_{Gon} = R_{Gon}(IGBT)$



switching losses (typical), Diode, Inverter

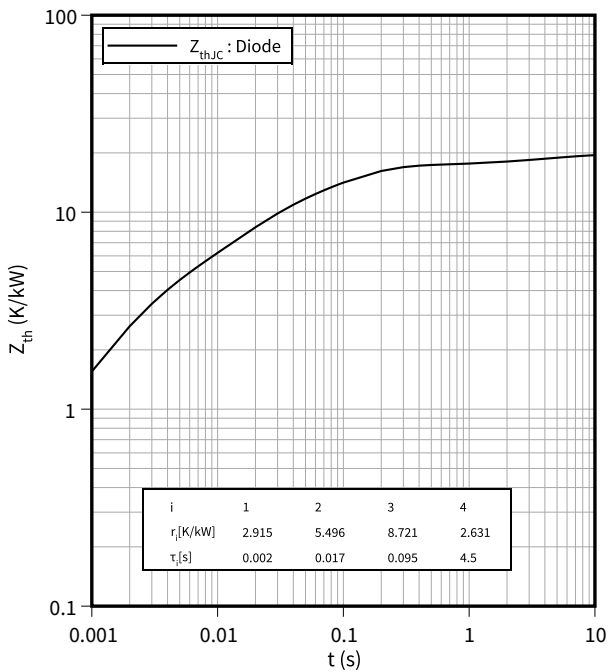
$E_{rec} = f(R_G)$

$V_{CE} = 1800\text{ V}$, $I_F = 1000\text{ A}$



transient thermal impedance , Diode, Inverter

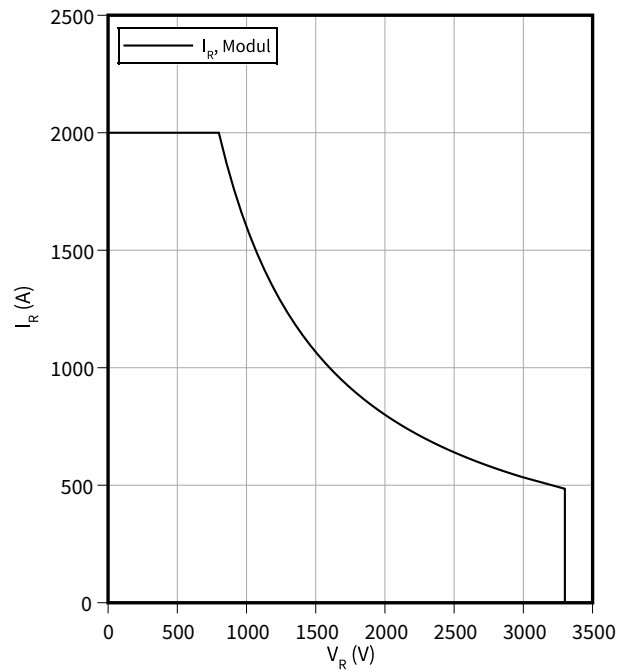
$Z_{th} = f(t)$



safe operation area (SOA), Diode, Inverter

$I_R = f(V_R)$

$T_{vj} = 150\text{ °C}$



5 Circuit diagram

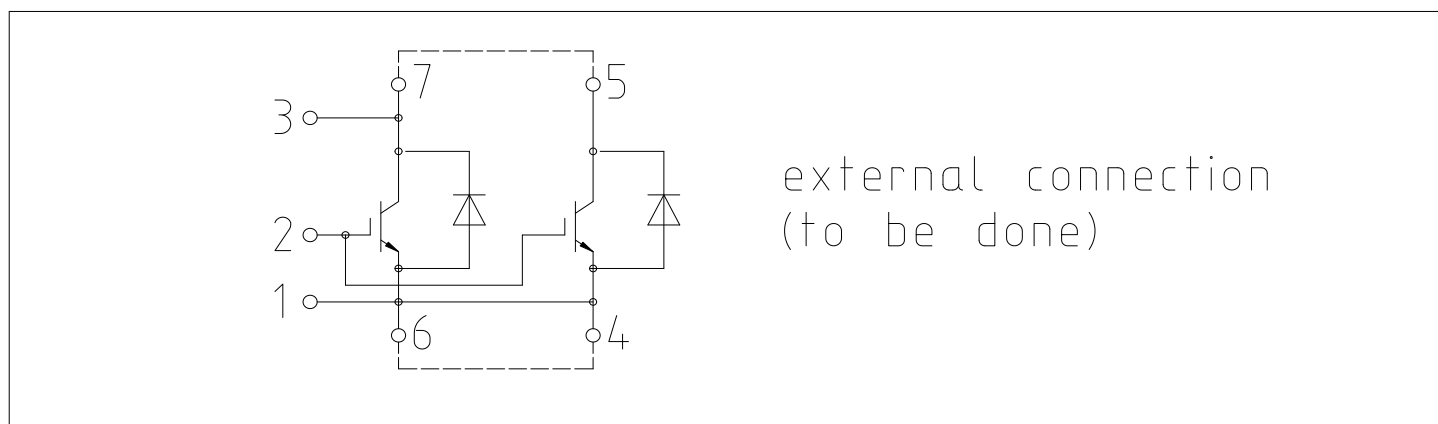


Figure 1

6 Package outlines

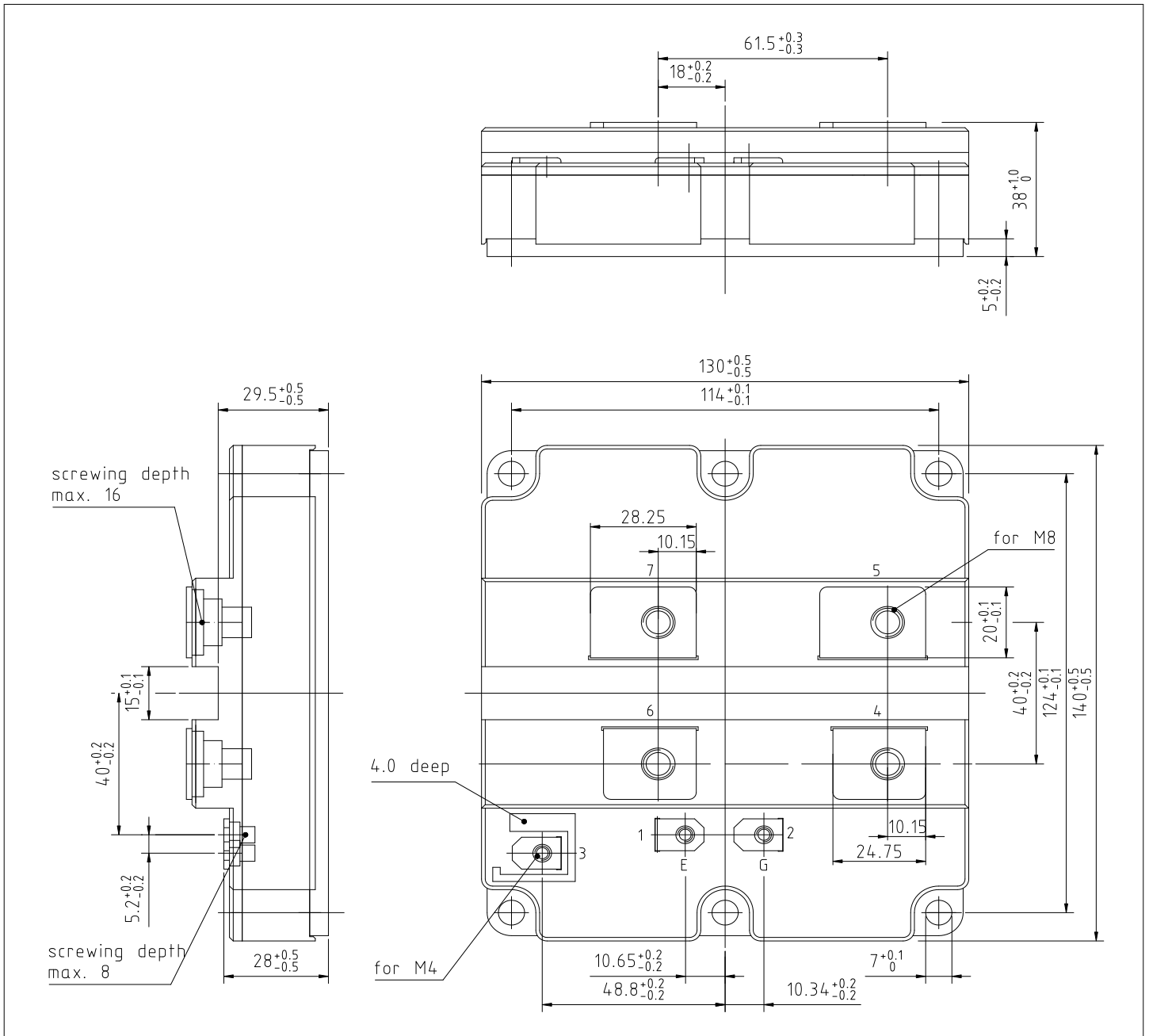


Figure 2

7 Module label code



Module label code			
Code format	Data Matrix	Barcode Code128	
Encoding	ASCII text	Code Set A	
Symbol size	16x16	23 digits	
Standard	IEC24720 and IEC16022	IEC8859-1	
Code content	Content	Digit	Example
	Module serial number	1 - 5	71549
	Module material number	6 - 11	142846
	Production order number	12 - 19	55054991
	Date code (production year)	20 - 21	15
	Date code (production week)	22 - 23	30
Example	 		
	71549142846550549911530		71549142846550549911530

Figure 3

Revision history

Document revision	Date of release	Description of changes
V2.0	2007-02-21	Preliminary datasheet
V2.1	2007-09-21	Preliminary datasheet
V2.2	2007-10-11	Preliminary datasheet
V2.3	2008-02-06	Preliminary datasheet
V2.4	2010-04-26	Preliminary datasheet
V3.0	2013-08-12	Final datasheet
V3.1	2013-12-11	Final datasheet
V3.2	2016-11-21	Final datasheet
V3.3	2018-07-12	Final datasheet
V3.4	2019-07-24	Final datasheet
n/a	2020-09-01	Datasheet migrated to a new system with a new layout and new revision number schema: target or preliminary datasheet = 0.xy; final datasheet = 1.xy
1.10	2021-10-28	Final datasheet

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